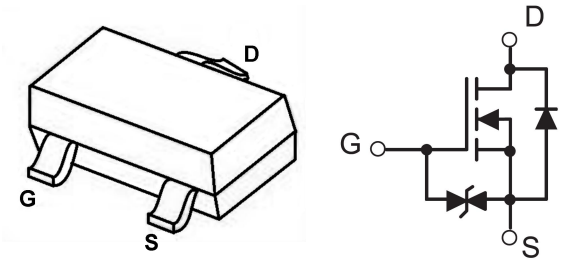
2SK3019TL

30V/0.1A N-Channel MOSFET

$V_{(BR)DSS}$	$R_{DS(on)}$MAX	I_D
30V	8Ω@4V	100mA
	13Ω@2.5V	

SOT-523



FEATURE

- Low on-resistance
- Fast switching speed
- Low voltage drive makes this device ideal for Portable equipment
- Easily designed drive circuits
- Easy to parallel

Order Information

Model	Marking	Package	shipping
2SK3019TL	**KN**	**SOT523**	**3000/Tape&Reel**

MOSFET MAXIMUM RATINGS (T_a = 25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Continuous Drain Current	0.1	A
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	833	℃ /W
P_D	Power Dissipation	0.15	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~+150	℃

30V/0.1A N-Channel MOSFET

MOSFET ELECTRICAL CHARACTERISTICS

T_a=25℃ unless otherwise specified

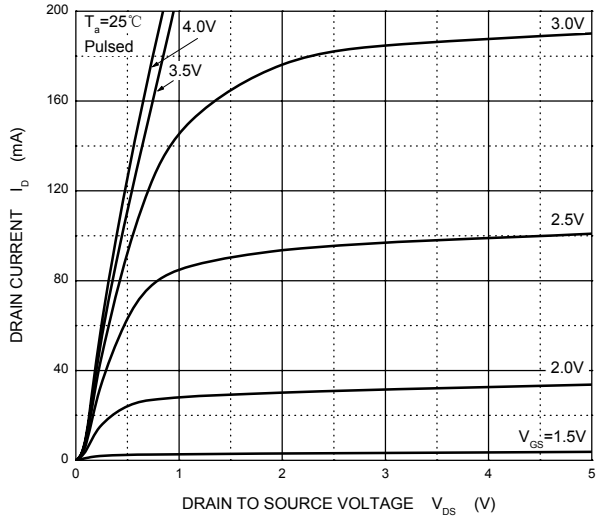
Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Off Characteristics						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0V, I_D = 10μA	30			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} =30V,V_{GS} = 0V			1	μA
Gate –Source leakage current	I_{GSS}	V_{GS} =±20V, V_{DS} = 0V			±2	μA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = 3V, I_D =100μA	0.8		1.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS} = 4V, I_D =10mA			8	Ω
		V_{GS} =2.5V,I_D =1mA			13	Ω
Forward Transconductance	g_{FS}	V_{DS} =3V, I_D = 10mA	20			mS
Dynamic Characteristics*						
Input Capacitance	C_{iss}	V_{DS} =5V,V_{GS} =0V,f =1MHz		13		pF
Output Capacitance	C_{oss}			9		pF
Reverse Transfer Capacitance	C_{rss}			4		pF
Switching Characteristics*						
Turn-On Delay Time	$t_{d(on)}$	V_{GS} =5V, V_{DD} =5V, I_D =10mA, Rg=10Ω, R_L=500Ω,		15		ns
Rise Time	t_r			35		ns
Turn-Off Delay Time	$t_{d(off)}$			80		ns
Fall Time	t_f			80		ns

* These parameters have no way to verify.

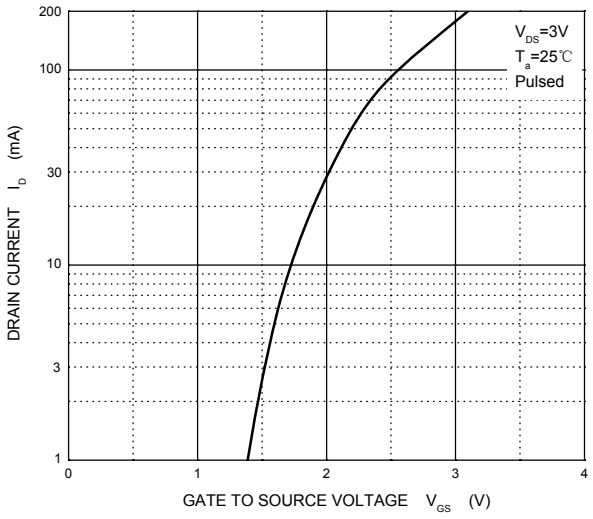
30V/0.1A N-Channel MOSFET

Typical Characteristics

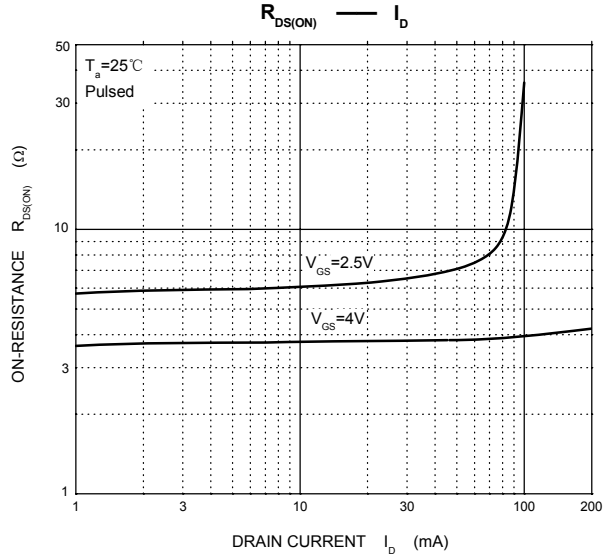
Output Characteristics



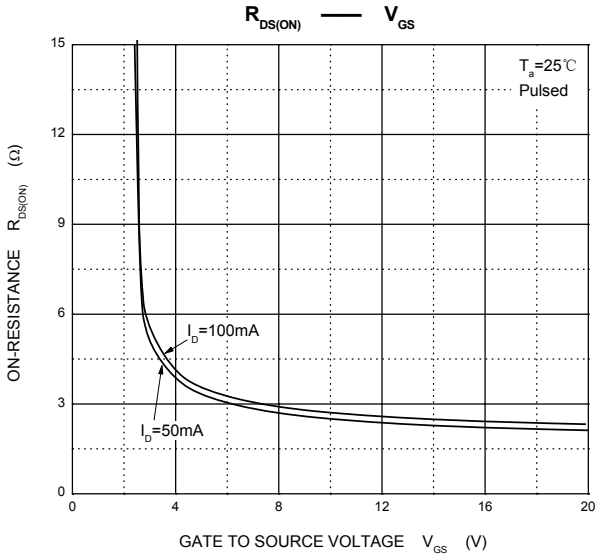
Transfer Characteristics



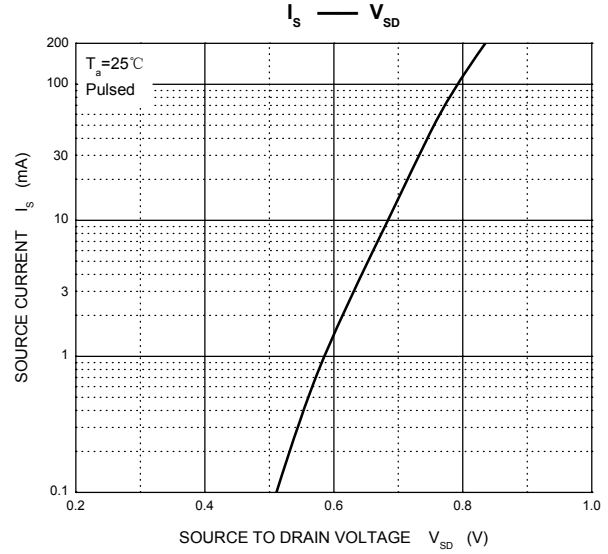
$R_{DS(ON)}$ — I_D



$R_{DS(ON)}$ — V_{GS}

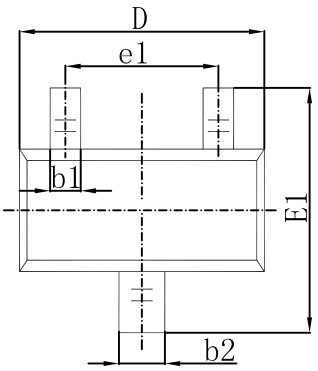


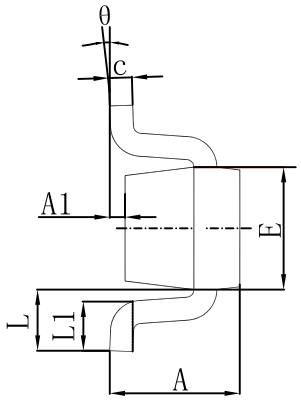
I_S — V_{SD}

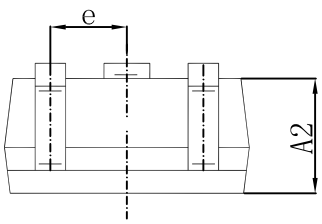


30V/0.1A N-Channel MOSFET

SOT-523 Package Outline Dimensions

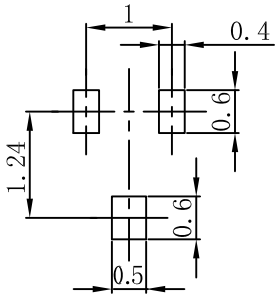






Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.350	0.010	0.014
c	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.700	0.900	0.028	0.035
E1	1.450	1.750	0.057	0.069
e	0.500 TYP.		0.020 TYP.	
e1	0.900	1.100	0.035	0.043
L	0.400 REF.		0.016 REF.	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

SOT-523 Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:±0.05mm.
3.The pad layout is for reference purposes only.